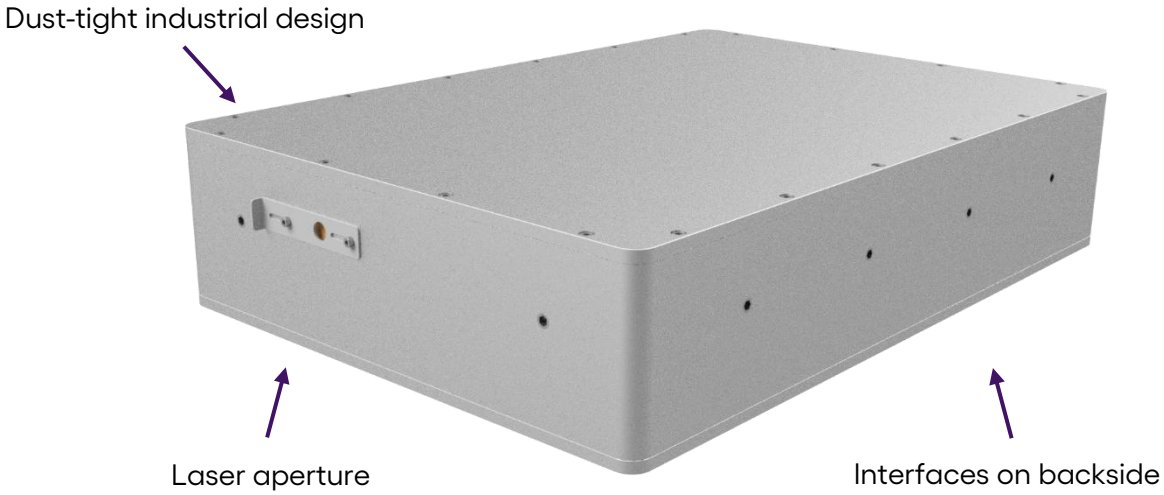
RayVen Laser GmbH
Universitätsstraße 150
44801 Bochum, Germany
rayvenlaser.com

RayVen-L

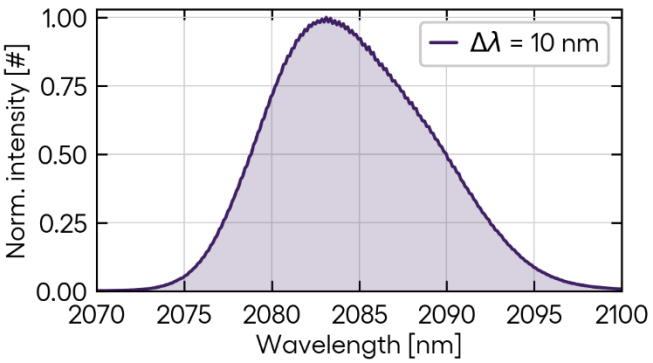
2.1 µm ultrafast amplifier system

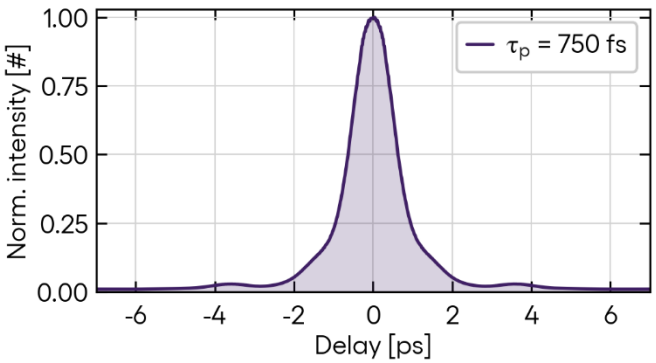


Specifications

- Pulse energy: 1 mJ – 100 µJ
- Repetition rate: 10 kHz – 100 kHz
- Average power: 10 W
- Pulse duration: 750 fs
- Wavelength: 2085 nm / 10 nm (-3dB)
- Beam quality: TEM_{00}, $M^2 < 1.2$
- Beam height: 80 mm
- Size (laser head): 470 x 322 x 112 mm^3
- All water-cooled

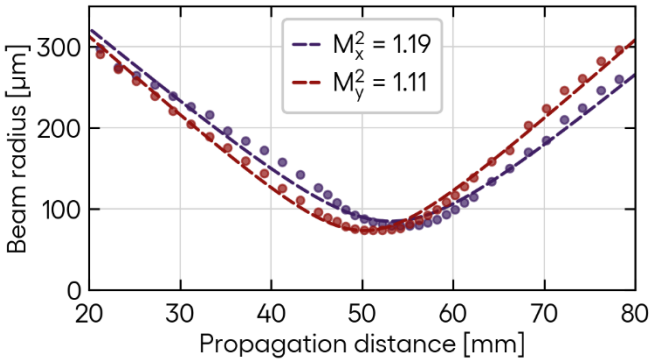
Pulse and spectral characterization (100 µJ)

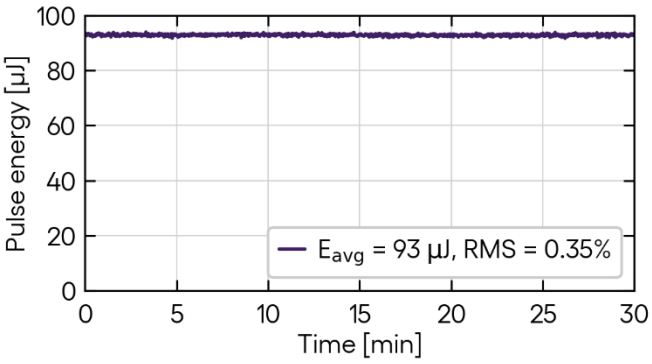




- Emission of a smooth spectrum and a close-to transform-limited pulse duration

Beam quality and power stability

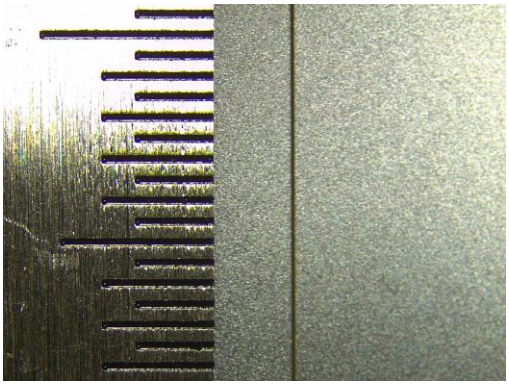




- Close-to diffraction-limited beam quality and high power stability

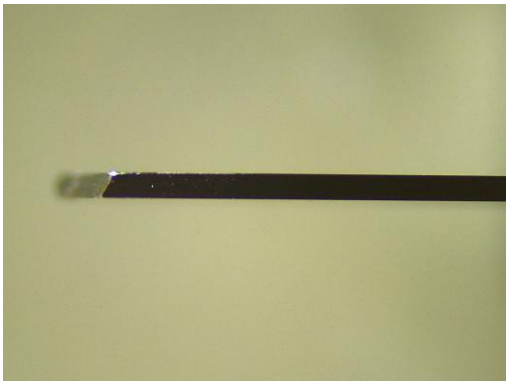
Materials processing

Scribing



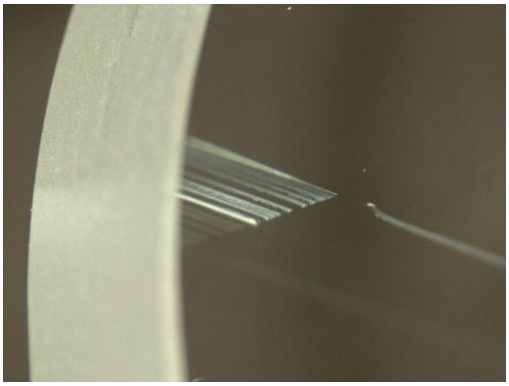
Silicon wafer, 350 µm thick, fine ground

Cleaving



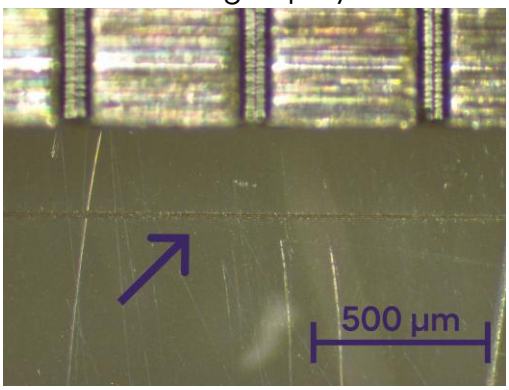
Silicon wafer, 350 µm thick, cleaved edge

In-volume modification



Corning 7979, 6.35 mm thick

Machining of polymers



Line scribe in PMMA (transparent)

Contacts

武汉莱速科技有限公司 www.laspeed.cn info@laspeed.cn 13545051195